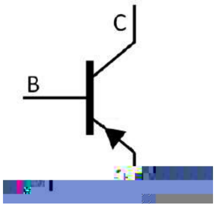
Rev.E Mar.-2016

WR0<5 ṂṂꓰ SQS ᴁṀ ӌ s ǁ ᒣ Silicon PNP transistor in a TO-92 Plastic Package.

High P_C and I_C.

Medium power amplifier applications.

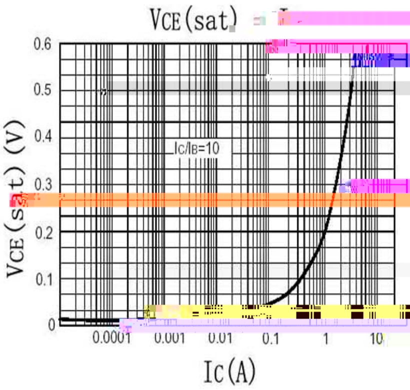


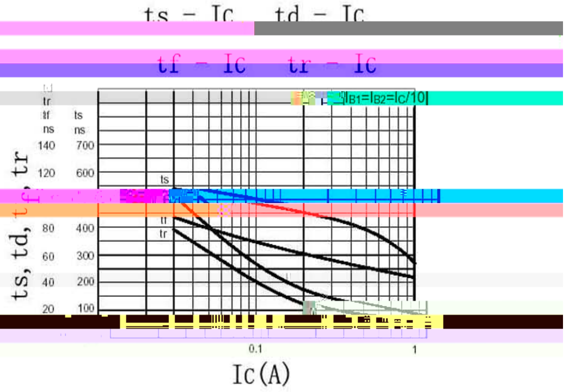
PIN1 χ Collector PIN 2 χ Base PIN 3 χ Emitter

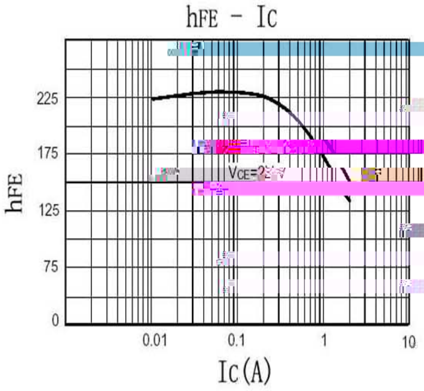
See Marking Instructions.

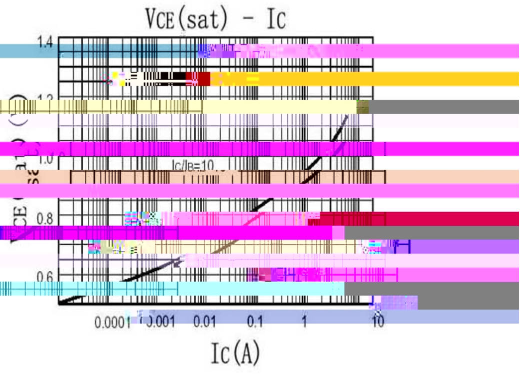
v ῼ Parameter	ɻ ᴺ Symbol	ῼ Ӫ Rating	ᴅ ɉ Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current- Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

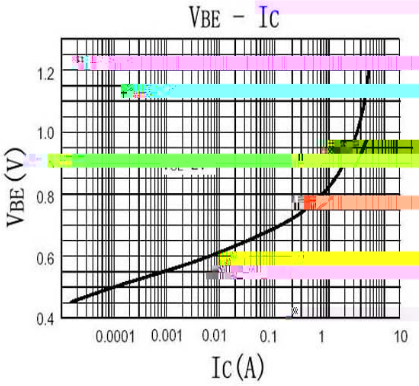
v ῼ Parameter	ɻ ᴺ Symbol	╜ ⁏ ꜍ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʓ Ӫ Typ	ῳ ⱬ Ӫ Max	ᴅ ɉ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA	-60			V
Collector to Emitter Breakdown Voltage	V	I =-10mA	-45			V

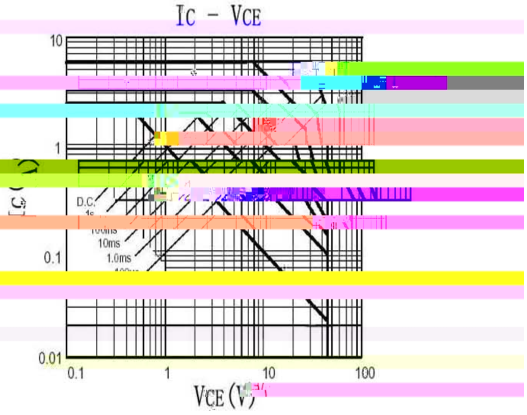

VCE(sat)
0.6
0.5
0.4
0.3
0.2
0.1
0
VCE(sat) (V)
Ic/IB=10
0.0001
0.001
0.01
0.1
1
10
Ic(A)

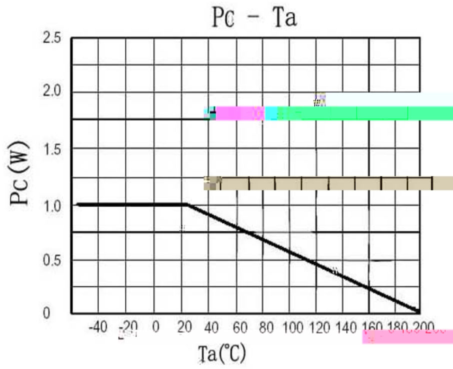

ts - Ic td - Ic
tf - Ic tr - Ic
IB1=IB2=Ic/10
td
tr
tf
ns
ts
ns
140
120
80
60
40
20
700
600
400
300
200
100
ts, td, tf, tr
ts
tf
tr
0.1
1
Ic(A)


hFE - Ic
225
175
125
75
0
hFE
VCE=2V
0.01
0.1
1
10
Ic(A)


VCE(sat) - Ic
1.4
1.0
0.8
0.6
Ic/IB=10
0.0001
0.001
0.01
0.1
1
10
Ic(A)

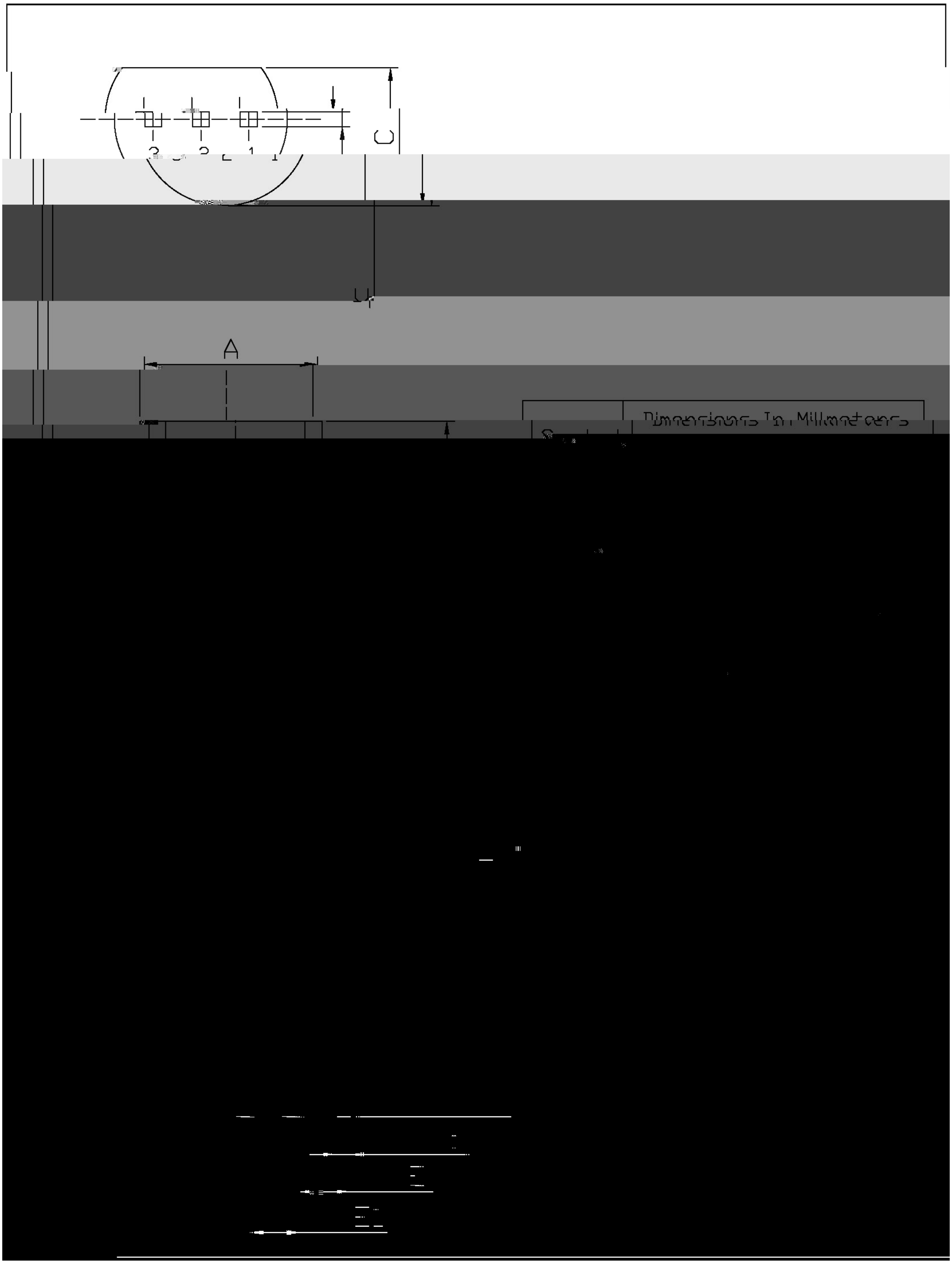

VBE - Ic
1.2
1.0
0.8
0.6
0.4
VBE (V)
0.0001
0.001
0.01
0.1
1
10
Ic(A)

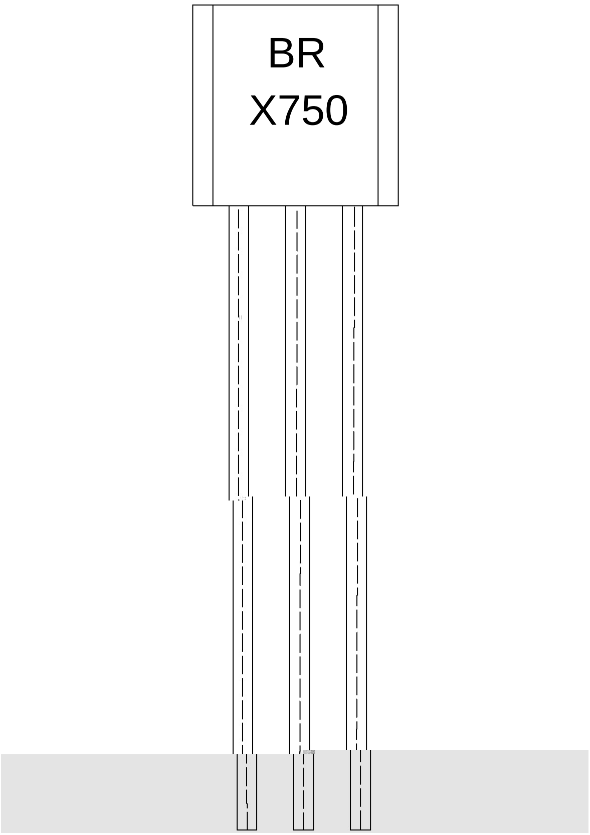

Ic - VCE
10
1
0.1
0.01
Ic (A)
D.C.
1s
100ms
10ms
1.0ms
0.1
1
10
100
VCE(V)


Pc - Ta
2.5
2.0
1.5
1.0
0.5
0
Pc (W)
-40
-20
0
20
40
60
80
100
120
140
160
180
200
Ta(℃)

TO-92

Unit: mm





ب ˝ χ

EU꞊	Ѭ ʅ ᴎ Ꮒ
[:83 χ	Ѭ ʒ ᴺ Ꮒ
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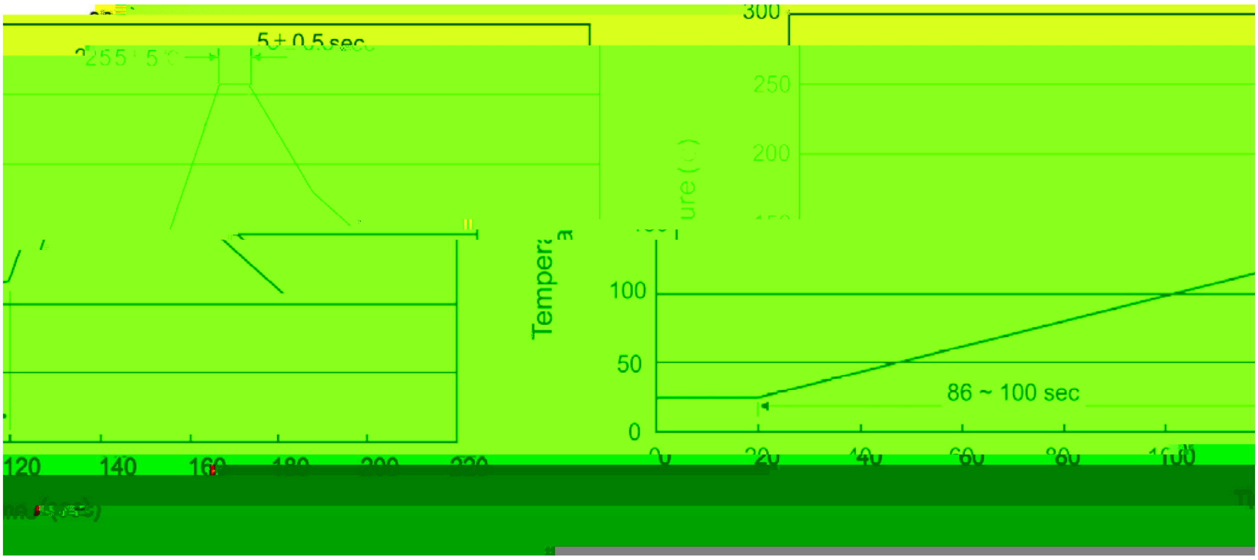
Note:

BR:	Company Code.
X750:	Product Type.
****:	Lot No. Code,code change with Lot No.



ب ˝ χ

1 ḯ ♬ □ ẙ 25 Ḱ 150 ɫ ı ῾H ڗ 60 Ḱ 90sec;

2 Ŝ Ӫ □ ẙ 255 ° 5 ɫ ı ῾H ڗ ῾Y ᎏ ᄧ 5 ° 0.5sec;

3 ỉ ˙ ˥ ˛ ͻ ಎ ẙ ᄧ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɫ /sec.

□ ẙ χ 270 ° 5 ɫ ῾H ڗ χ 10 ° 1 sec.

Temp:270±5 Time:10±1 sec

῞Ω ҭ ɣ Ŀ / BULK

Package Type	Units					Dimension		(unit mm3)

ᄉ Ṿ ɣ Ŀ / AMMO

Package Type	Units					Dimension		(unit mm3)